

## KOREAN PATENT ABSTRACTS

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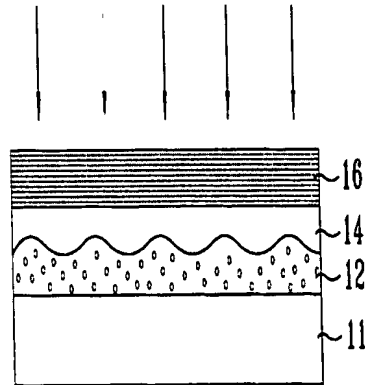
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(54) METHOD OF FORMING POLYSILICON LAYER OF POLYSILICON THIN FILM TRANSISTOR

(57) Abstract:

PURPOSE: The method increases the mobility of a polysilicon layer.

CONSTITUTION: The method comprises the steps of: forming a first buffer layer(12) of low thermal conductivity on a glass substrate(11); forming a second buffer layer(14) of an insulation film such as SiO<sub>2</sub>, SiON or Si<sub>3</sub>N<sub>4</sub>; planarizing the second buffer layer; forming an amorphous silicon layer on the planarized second buffer layer; performing the dehydrogenation process as to the amorphous silicon layer; and performing the crystallization process as to the amorphous silicon layer.



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Legal Status

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